

Vishay Siliconix

## N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)		
40	0.045 at V <sub>GS</sub> = 10 V	3.9		
	0.058 at V <sub>GS</sub> = 4.5 V	3.5		

### **FEATURES**

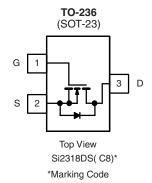
- Halogen-free According to IEC 61249-2-21
  Available
- TrenchFET<sup>®</sup> Power MOSFET

### **APPLICATIONS**

- Stepper Motors
- Load Switch



COMPLIANT HALOGEN FREE Available



Ordering Information: Si2318DS-T1-E3 (Lead (Pb)-free) Si2318DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	A = 25 °C, unles	ss otherwise r	oted		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	40		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Continuous Drain Correct (T 150 %0) <sup>a, b</sup>	T <sub>A</sub> = 25 °C	– I <sub>D</sub>	3.9	3.0	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a, b</sup>	T <sub>A</sub> = 70 °C		3.1	2.4	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	16		A
Continuous Source Current (Diode Conduction) <sup>a, b</sup>		۱ <sub>S</sub>	0.8		
	T <sub>A</sub> = 25 °C	– P <sub>D</sub>	1.25	0.75	W
Power Dissipation <sup>a, b</sup>	T <sub>A</sub> = 70 °C		0.8	0.48	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum lunction to Ambienta	t ≤ 5 s	R <sub>thJA</sub>	75	100	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		120	166	°C/W
Maximum Junction-to-Foot (Drain)	Steady State		40	50	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature

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## Si2318DS

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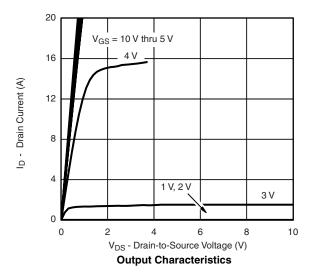


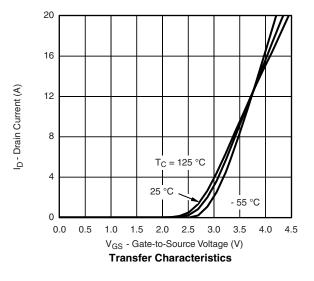
			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS}$ = 0 V, $I_D$ = 250 $\mu$ A	40			v	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1		3		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 32 V, V_{GS} = 0 V$	= 0 V		0.5		
		$V_{DS}$ = 32 V, $V_{GS}$ = 0 V, $T_{J}$ = 55 °C			10	μA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 4.5$ V, $V_{GS} = 10$ V	6			Α	
	R <sub>DS(on)</sub>	$V_{GS} = 10$ V, $I_{D} = 3.9$ A		0.036	0.045		
Drain-Source On-Resistance <sup>a</sup>		$V_{GS} = 4.5 \text{ V}, I_D = 3.5 \text{ A}$		0.045	0.058	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 3.9 \text{ A}$		11		S	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1.25 A, V <sub>GS</sub> = 0 V		0.8	1.2	V	
Dynamic <sup>b</sup>			1		1 1		
Total Gate Charge	Qg			10	15	nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ = 20 V, $V_{GS}$ = 10 V, $I_{D}$ = 3.9 A		1.6			
Gate-Drain Charge	Q <sub>gd</sub>			2.1			
Gate Resistance	Rg			1.8		Ω	
Input Capacitance	C <sub>iss</sub>			540			
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ = 20 V, $V_{GS}$ = 0 V, f = 1 MHz		80		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			45			
Switching	· ·						
Turn-On Delay Time	t <sub>d(on)</sub>			5	10	nc	
Rise Time	t <sub>r</sub>	$V_{DD}$ = 20 V, $R_L$ = 20 $\Omega$		12	20		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ 1.0 A, $V_{GEN}$ = 10 V, $R_G$ = 6 $\Omega$		20	30	ns	
Fall Time	t <sub>f</sub>			15	25		

a. Pulse test; PW  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





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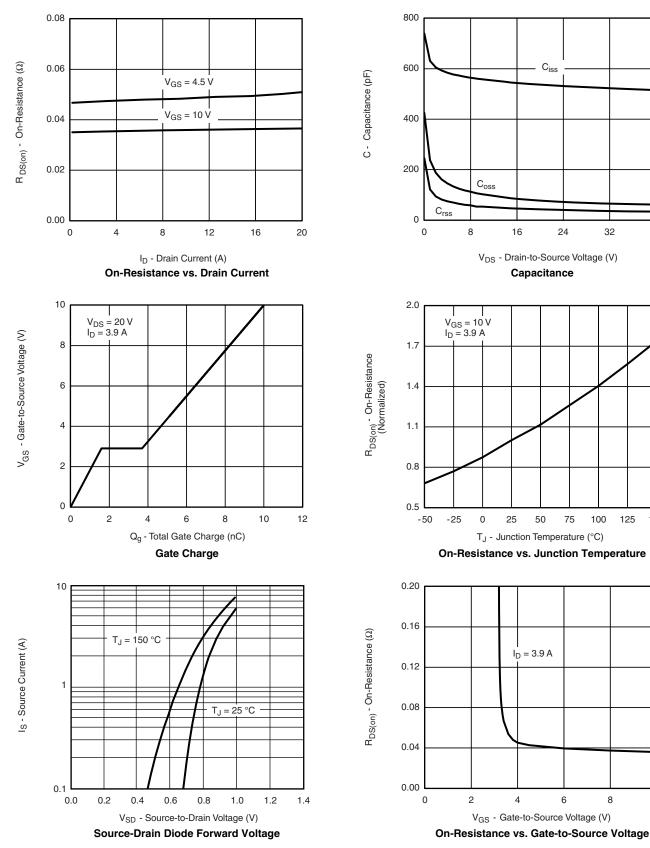
# Si2318DS

40

150

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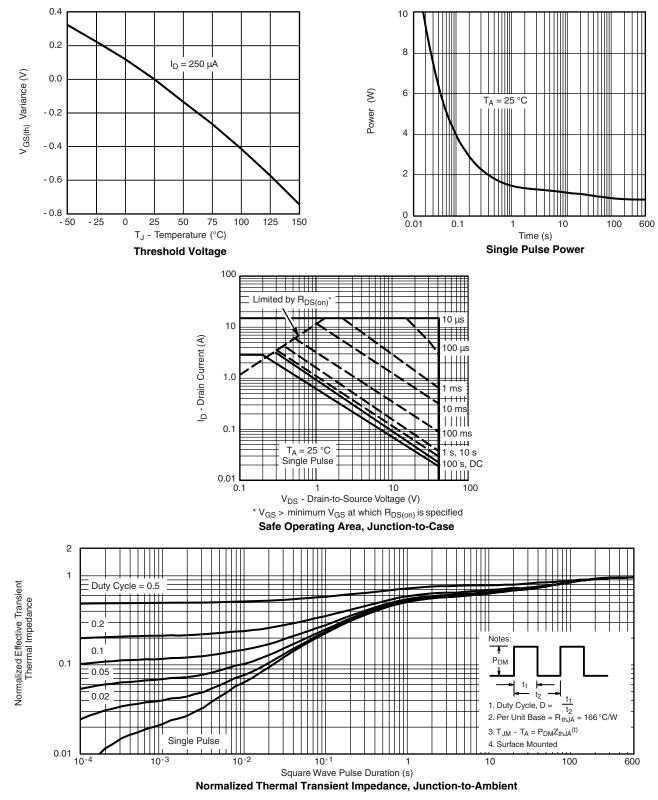
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Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?72322</u>.

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